

YJ Planar Schottky Barrier Diode Die Specification

20V 0.5A, 25mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB025L020AS-180A

Main Products Characterstics

- Average forward current: IF(AV) = 0.5 A
- Maximum operating junction temperature: Tj = 125 °C
- Top metal: AL

Maximum Ratings

Non-repetitive peak surge current
(tp = 8.3 ms, halfwave, 1 cycle)

Static Electrical Characteristics (Ta = 25°C)

			Value	
			Spec	Typical
			20 V	36V
Maximum forward voltage drop				
	IF = 0.5A	VF	0.44V	0.42V
Pulse Test: tp = 300 μs, δ ≤ 2%				
			150uA	5uA

Device Schematics and Outline Drawing

Die Thickness *	7Mils
Die Size **	
Top Metal Pad	23Mils
Active Area	18.8 Mils
Top Metal	AL
Back Metal	

Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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